NSN 5961-00-401-6652

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Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-401-6652 **Inclosure Material:** Metal **Overall Length:** Between 0.140 inches and 0.260 inches **Terminal Length:** 1.500 inches **Overall Diameter:** Between 0.335 inches and 0.370 inches **Component Name And Quantity:** 2 transistor **Mounting Method: Terminal Terminal Circle Diameter:** 0.200 inches **Features Provided:** Burn in **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 60.0 breakdown voltage, collector-to-base, emitter open all transistor and 7.0 emitter to base voltage, static, collector open all transistor and 30.0 collector-to-emitter, substaining voltage, base open-circuited all transistor **Power Rating Per Characteristic:** 200.0 milliwatts small-signal input power, common-collector absolute all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: npn **Terminal Type And Quantity:** 6 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No